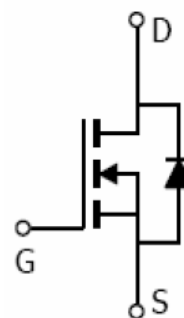
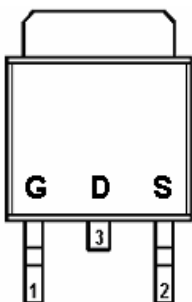
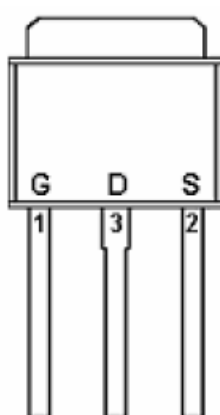


DESCRIPTION

ST484D is the N-Channel logic enhancement mode power field effect transistor which is produced using high cell density, DMOS trench technology. The ST484D has been designed specially to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $R_{DS(ON)}$ and fast switching speed.

FEATURE

- 30V/20.0A, $R_{DS(ON)} = 8m\Omega$ (Typ.)
@ $V_{GS} = 10V$
- 30V/15.0A, $R_{DS(ON)} = 12m\Omega$
@ $V_{GS} = 4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- TO-252, TO-251 package design

**PIN CONFIGURATION****TO-252****TO-251**

30A N Channel Enhancement Mode MOSFET

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	VDSS	30	V
Gate-Source Voltage	VGSS	±20	V
Continuous Drain Current (TJ=150°C)	ID	30.0 20.0	A
		TA=25°C TA=70°C	
Pulsed Drain Current	IDM	80	A
Continuous Source Current (Diode Conduction)	IS	21	A
Power Dissipation	PD	50 25	W
		TA=25°C TA=70°C	
Operation Junction Temperature	TJ	150	°C
Storage Temperature Range	TSTG	-55/150	°C
Thermal Resistance-Junction to Ambient	RθJA	60	°C/W

ELECTRICAL CHARACTERISTICS (Ta = 25°C Unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250uA	30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1.0		2.5	V
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =24V, V _{GS} =0V			1	uA
		V _{DS} =24V, V _{GS} =0V T _J =55°C			5	
On-State Drain Current	I _{D(on)}	V _{DS} ≥ 5V, V _{GS} =10V	80			A
Drain-source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A		8	13	mΩ
		V _{GS} =4.5V, I _D =15A		12	18	
Forward Transconductance	g _{fs}	V _{DS} =5V, I _D =12A		25		S
Diode Forward Voltage	V _{SD}	I _S =1.0A, V _{GS} =0V			1.2	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =10V, V _{DS} =15V I _D =20A		19	22	nC
Gate-Source Charge	Q _{gs}			3.2		
Gate-Drain Charge	Q _{gd}			4.5		
Input Capacitance	C _{iss}	V _{DS} = 20V, V _{GS} =0V F=1MHz		950		pF
Output Capacitance	C _{oss}			145		
Reverse Transfer Capacitance	C _{rss}			99		
Turn-On Time	t _{d(on)}	V _{DD} =20V, R _L = 4Ω I _D =5.0A, V _{GEN} =10V R _G =1Ω		6		nS
	t _r			12		
Turn-Off Time	t _{d(off)}			20		
	t _f			6		

TYPICAL CHARACTERISTICS

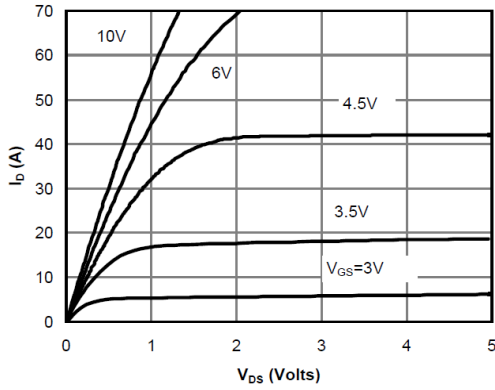


Figure 1: On-Region Characteristics

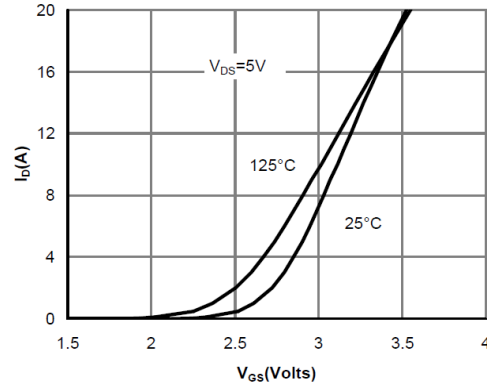


Figure 2: Transfer Characteristics

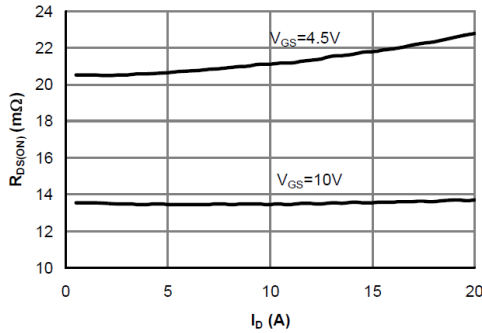


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

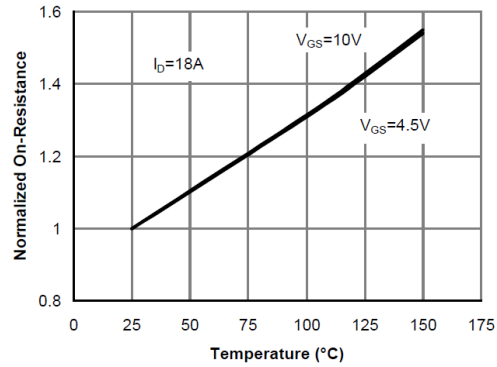


Figure 4: On-Resistance vs. Junction Temperature

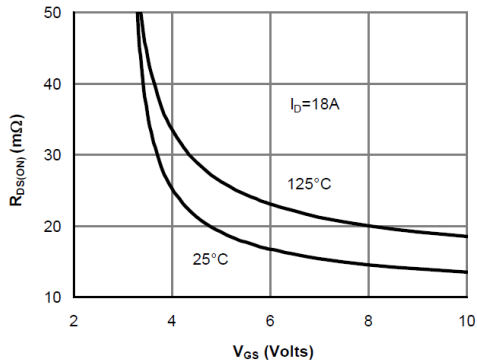


Figure 5: On-Resistance vs. Gate-Source Voltage

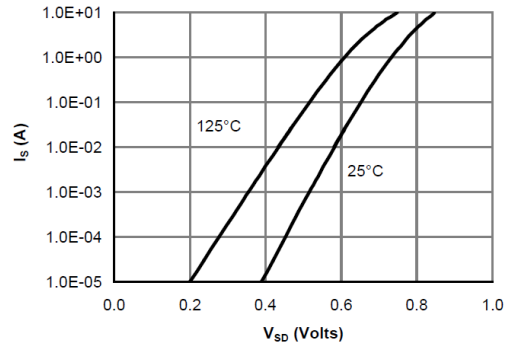


Figure 6: Body-Diode Characteristics

TYPICAL CHARACTERISTICS

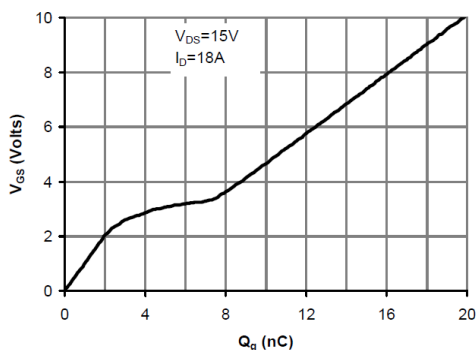


Figure 7: Gate-Charge Characteristics

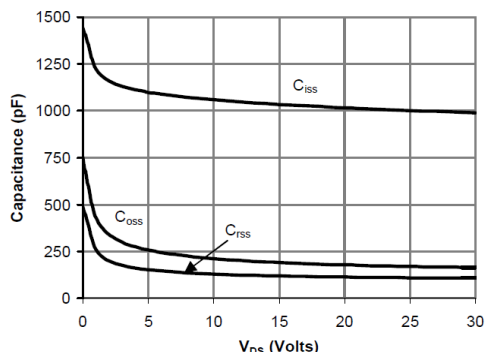


Figure 8: Capacitance Characteristics

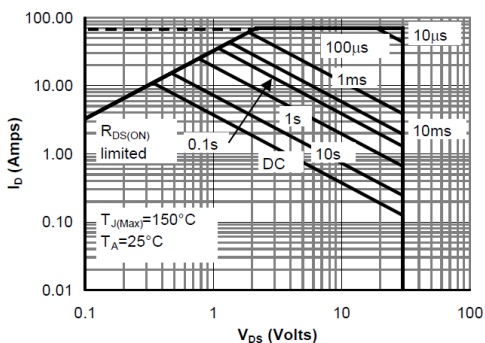


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

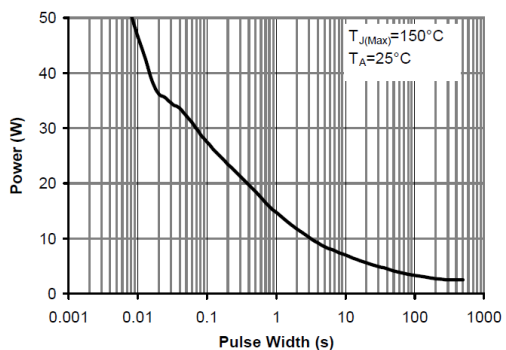


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

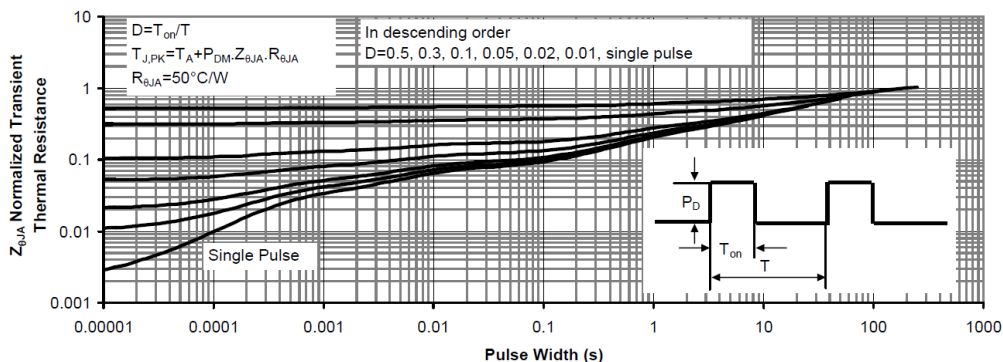
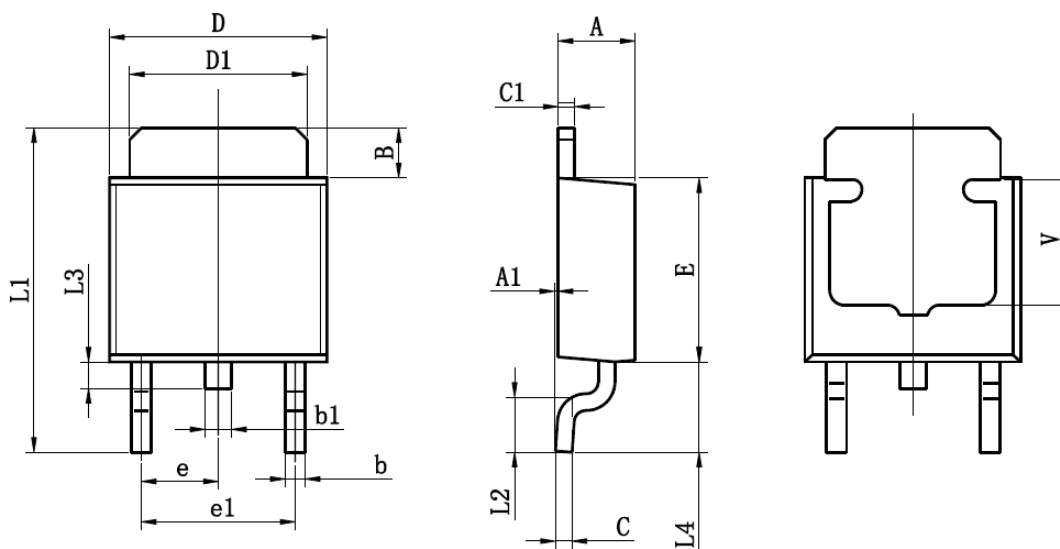


Figure 11: Normalized Maximum Transient Thermal Impedance

TO-252-2L PACKAGE OUTLINE SOP-8P



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300TYP		0.091TYP	
e1	4.500	4.700	0.177	0.185
L1	9.500	9.900	0.374	0.390
L2	1.400	1.780	0.055	0.070
L3	0.650	0.950	0.026	0.037
L4	2.550	2.900	0.100	0.114
V	3.80REF		0.150REF	